



**ANALOG
DEVICES**

Fast, Complete Sampling 14-Bit A/D Converter with Microprocessor Interface

AD679

1.1 Scope.

This specification covers the detail requirements for a 14-bit resolution A/D converter with complete microprocessor interface and an on-chip sample-hold amplifier.

1.2 Part Number.

The complete part number per Table 1 of this specification is as follows:

Device	Part Number ¹
-1	AD679SX/883B
-2	AD679TX/883B

NOTE

¹See paragraph 1.2.3 for package identifier.

1.2.3 Case Outline.

Appendix 1 of General Specification ADI-M-1000: package outline:

Type	Package	Description
D	D-28	28-Pin DIP
J	J-44	44-Pin JLCC

1.3 Absolute Maximum Ratings. (T_A = +25°C unless otherwise noted)

V _{CC} to AGND	+18 V to -0.3 V
V _{EE} to AGND	-18 V to +0.3 V
V _{DD} to DGND	0 V to +7 V
AGND to DGND	-1 V to +1 V
V _{CC} to V _{EE}	+26.4 V to -0.3 V
A _{IN} , REF _{IN} to AGND	V _{EE} to V _{CC}
Digital Inputs to DGND	-0.5 V to +7 V
Digital Outputs to DGND	-0.5 V to V _{DD} + 0.3 V
Power Dissipation	1000 mW
Storage Temperature Range	-65°C to +150°C
Lead Temperature (Soldering 10 sec)	+300°C

1.5 Thermal Characteristics.

Thermal Resistance θ_{JC} = 4°C/W for J-44; 25°C/W for D-28

θ_{JA} = 80°C/W for J-44; 60°C/W for D-28

Tested in accordance with MIL-STD-750C in still air freely suspended under natural convection conditions.

REV. A

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AD679 — SPECIFICATIONS

Table 1.

Test	Symbol	Device	Design Limit @ +25°C	Sub Group 1	Sub Group 2, 3	Test Condition ¹	Units
Power Dissipation	P _D	-1, 2	745	745	745	Converting	mW max
Internal Reference Output Voltage	V _{REF}	-1, 2	4.98	4.98	4.98	Bipolar 0.5 mA External Load	+V min
			5.02	5.02	5.02		+V max
Internal Reference Output Current	I _{REF}	-1, 2	1.5	1.5	1.5	Unipolar	mA max
			0.5	0.5	0.5	Bipolar	
High Level Input Voltage	V _{IH}	-1, 2	2.0	2.0	2.0		+V min
Low Level Input Voltage	V _{IL}	-1, 2	0.8	0.8	0.8		+V max
Logic Input Current	I _{IH}	-1, 2	10	10	10	V _{IH} = 5.0 V V _{IL} = 0.0 V	±μA max
High Level Output Voltage	V _{OH}	-1, 2	2.4	2.4	2.4	I _{OH} = -0.5 mA	+V min
Low Level Output Voltage	V _{OL}	-1, 2	0.4	0.4	0.4	I _{OL} = 1.6 mA	+V max
High Z Leakage Current	I _{OZ}	-1, 2	10	10	10	V _{IN} = 0, V _{DD}	±μA max
Power Supply Current	I _{CC}	-1, 2	20	20	20	V _{CC} = 12.6 V	mA max
	I _{EE}	-1, 2	-34	-34	-34	V _{EE} = -12.6 V	
	I _{DD}	-1, 2	12	12	12	V _{DD} = +5.5 V	
Integral Nonlinearity	INL	-2	2	2	2	Unipolar	±LSB max
Differential Nonlinearity ²	DNL	-1, 2	14	14	14	All Codes Tested	Bits min
Unipolar Zero Error	ZE _U	-2	11.5	11.5			±LSB max
Bipolar Zero Error	ZE _B	-2	11.5	11.5			±LSB max
Unipolar Zero Error Drift	ZE _{U,TC}	-2			16.4	w/Internal Reference	±LSB max
Bipolar Zero Error Drift	ZE _{B,TC}	-2			14.7	w/Internal Reference	±LSB max
Gain Error	GE	-2	18	18		Unipolar & Bipolar Modes	±LSB max
Gain Error Drift	GETC	-2			16.4	Unipolar Mode w/External Reference	±LSB max
Gain Error Drift	GETC	-2			41	Unipolar & Bipolar Mode w/Internal Reference	±LSB max
Power Supply Rejection Ratio	PSRR	-2	6	6	6	Unipolar Mode ³	±LSB max
Signal-to-Noise and Distortion	S/(N+D)	-1	78	78	78	Bipolar, f _{IN} = 10.06 kHz	dB min
		-2	78	78	78	Bipolar, f _{IN} = 10.06 kHz	
Total Harmonic Distortion	THD	-1, 2	-84	-82	-82	Bipolar, f _{IN} = 10.6 kHz	-dB max
Intermodulation Distortion Second-Order Products	IMD ₂	-1, 2	-84	-84	-84	Bipolar, f _A = 9.09 kHz; f _B = 9.58	-dB max
Intermodulation Distortion Third-Order Products	IMD ₃	-1, 2	-84	-84	-84	Bipolar, f _A = 9.09 kHz; f _B = 9.58	-dB max
SC Delay	t _{SC}	-1, 2	50	50	50	See Figure 1	ns min
Conversion Rate	t _{CR}	-1, 2	7.8	7.8	7.8	See Figure 1	μs max
Convert Pulse Width	t _{CP}	-1, 2	97	97	97	See Figure 1	ns min
Conversion Time	t _C	-1, 2	6.3	6.3	6.3	See Figure 1	μs max
Status Delay	t _{SD}	-1, 2	0	0	0	See Figure 1	ns min
			400	400	400		ns max
Access Time	t _{BA}	-1, 2	100	100	100	See Figures 2, 3, 4	ns max
Float Delay	t _{FD}	-1, 2	10	10	10	See Figures 2, 3, 4	ns min
			80	80	80		ns max
Format Setup	t _{FS}	-1, 2	100	100	100	See Figure 3	ns min
OE Delay	t _{OE}	-1, 2	20	20	20	See Figure 3	ns min
Read Pulse Width	t _{RP}	-1, 2	195	195	195	See Figure 3	ns min
Conversion Delay	t _{CD}	-1, 2	400	400	400	See Figures 1, 3	ns min
EOCEN Delay	t _{EO}	-1, 2	50	50	50	See Figure 2	ns min

NOTES

¹ $V_{CC} = +12\text{ V} \pm 5\%$, $V_{EE} = -12\text{ V} \pm 5\%$, $V_{DD} = 5\text{ V} \pm 10\%$. See Figures 1, 2, 3, and 4 for timing information.

²Minimum resolution for which no missing codes are guaranteed.

³Test condition for PSRR, with limit shown as the change from nominal value to each extreme:

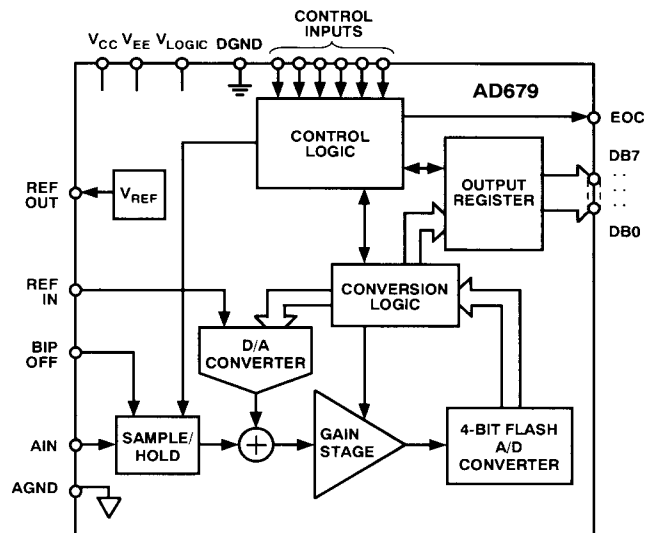
+11.4 V $\leq V_{CC} \leq$ +12.6 V; $V_{EE} = -12\text{ V}$; $V_{DD} = +5\text{ V}$

-12.6 V $\leq V_{EE} \leq$ -11.4 V; $V_{CC} = +12\text{ V}$; $V_{DD} = +5\text{ V}$

+4.5 V $\leq V_{DD} \leq$ +5.5 V; $V_{CC} = +12\text{ V}$; $V_{EE} = -12\text{ V}$

3.2.1 Functional Block Diagram and Terminal Assignments.

Description	D-Pin Description	J-44 Pin Description
EOCEN	1	1
$\overline{\text{OE}}$	2	3
$\overline{\text{SC}}$	3	5
$\overline{\text{CS}}$	4	6
V_{EE}	5	8
AIN	6	10
AGND	7	11
REFOUT	8	12
REF _{IN}	9	14
BIPOFF	10	15
V_{CC}	11	17
DGND	12	19
SYNC	13	21
DGND	14	23
$\overline{\text{HBE}}$	15	25
V_{DD}	16	26
V_{DD}	17, 18	27, 30
DB0	19	31
DB1	20	33
DB2	21	34
DB3	22	35
DB4	23	36
DB5	24	37
DB6	25	39
DB7	26	40
EOC	27	42
V_{DD}	28	43



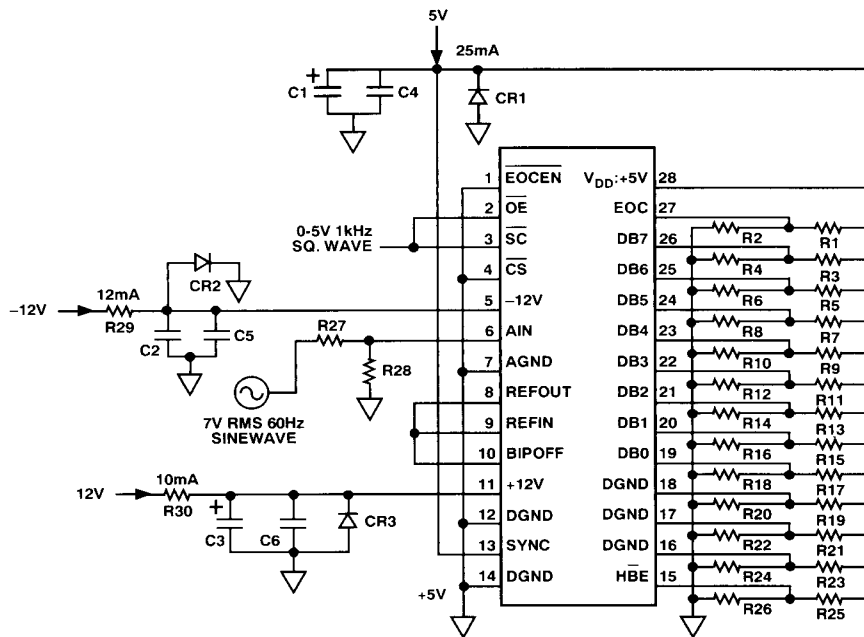
3.2.4 Microcircuit Technology Group.

This circuit is covered by technology group (57).

AD679

4.2.1 Life Test/Burn-In Circuit.

Steady state life test is per MIL-STD-883 Method 1005. Burn-in is per MIL-STD-883 Method 1015 test condition (B).



NOTES

1. C1, C2, C3 ARE 47 μ F CAPACITORS RATED AT 35V, 125°C.
2. C4, C5, C6 ARE 0.1 μ F CAPACITORS RATED AT 50V, 125°C.
3. CR1, CR2, CR3 ARE MRB20 DIODES.
4. R1-R26 ARE 3k Ω RESISTOR PACKS.
5. ALL CURRENTS SHOWN ARE MAXIMUM PER DEVICE.
6. R27, R28 ARE 10k Ω 1% 1/4 WATT METAL FILM RESISTORS.
7. R29 AND R30 ARE 1 Ω 2 WATT GLASS RESISTORS.

Burn-In Circuit

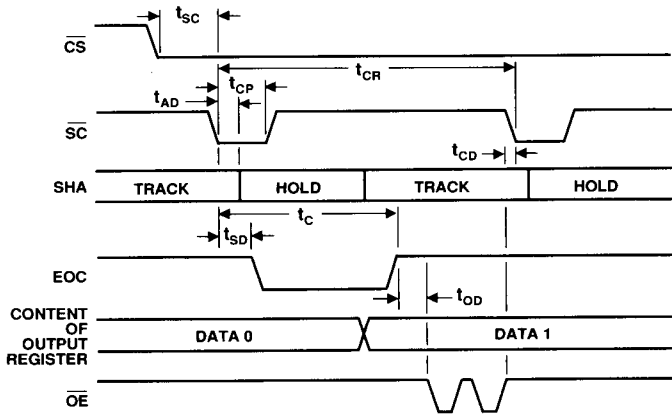


Figure 1. Conversion Timing

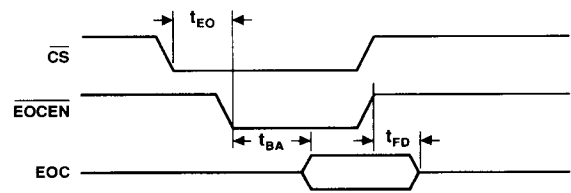
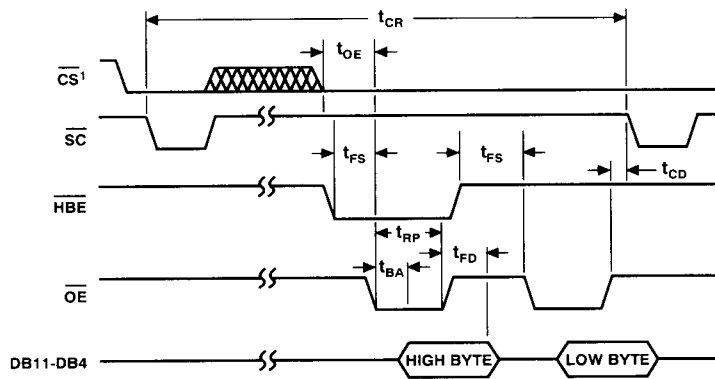


Figure 2. EOC Timing



NOTE
¹ IN ASYNCHRONOUS MODE, \overline{SC} IS INDEPENDENT OF \overline{CS} .

Figure 3. Output Timing

TIME	V_{CP}	C_{OUT}
ACCESS TIME HIGH Z TO LOGIC LOW	5V	100pF
FLOAT TIME LOGIC HIGH TO HIGH Z	0V	10pF
ACCESS TIME HIGH Z TO LOGIC HIGH	0V	100pF
FLOAT TIME LOGIC LOW TO HIGH Z	5V	10pF

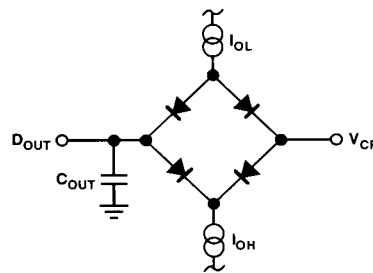
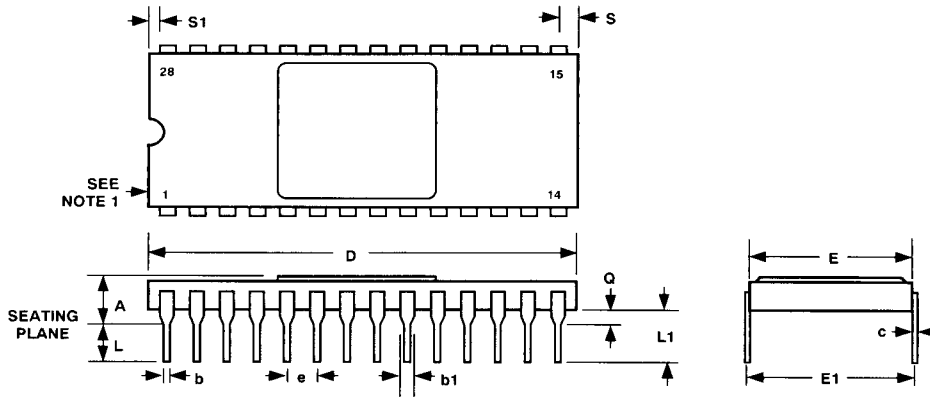


Figure 4. Load Circuit for Bus Timing Specifications

D-28

28-Pin Side Brazed Ceramic DIP



SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	-	0.232	-	5.84	6
b	0.014	0.023	0.36	0.58	
b1	0.038	0.065	0.96	1.65	2,6
c	0.008	0.015	0.20	0.38	6
D	-	1.490	-	37.85	4
E	0.500	0.610	12.70	15.49	4
E1	0.590	0.620	14.99	15.75	-
e	0.100BSC		2.54BSC		7
L	0.125	0.200	3.18	5.08	-
L1	0.150	-	3.81	-	-
Q	0.015	0.060	3.38	1.52	3
S	-	0.100	-	2.54	5
S1	0.005	-	0.13	-	5

NOTES

1. Index area; a notch or a lead one identification mark is located adjacent to the lead one.
2. The minimum limit for dimension b1 may be 0.023" (0.58 mm) for all four corner leads only.
3. Dimension Q shall be measured from the seating plane to the base plane.
4. This dimension allows for off-center lid, meniscus and glass overrun.
5. Applies to all four corners.
6. All leads - increase maximum limit by 0.003" (0.008 mm) measured at the center of the flat, when hot solder dip lead finish is applied.
7. Twenty-six spaces.

